ICP-RIE etching The Effect of CH_4/H_2 Gas Admixture on the Selectivity towards Pt in Dry Etching of PZT Thin-Films by ICP-RIE

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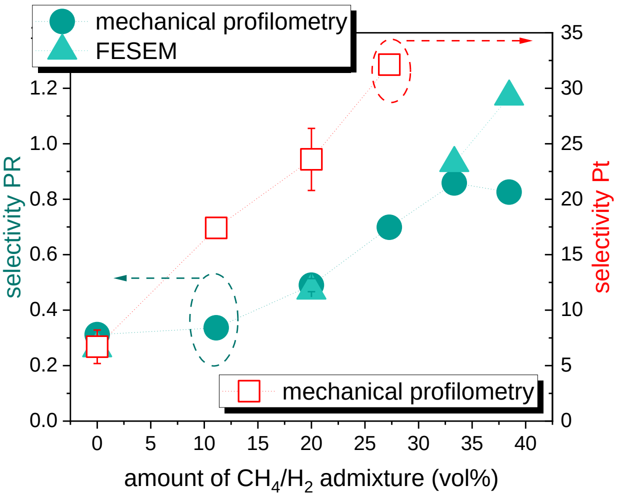

Figure 1: *Selectivity towards Pt and PR (AZ ECI 3027) during ICP-RIE of PZT in $CH_3F/Cl_2/BCl_3$ plasma with increasing amount of CH_4/H_2 admixture*

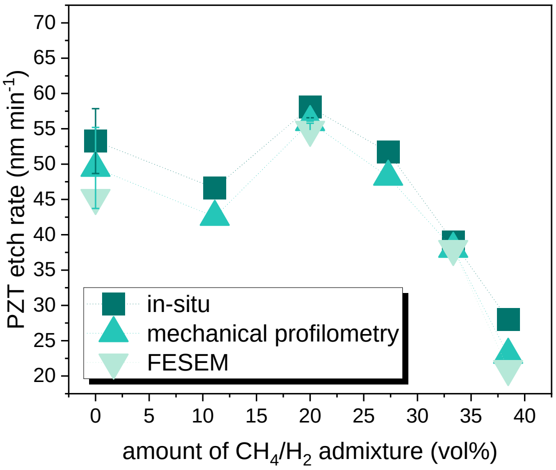

Figure 2: *PZT etch rate during ICP-RIE in $CH_3F/Cl_2/BCl_3$ plasma with increasing amount of CH_4/H_2 admixture*

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